

200547US-2



IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

HIDEYO OKUSHI ET AL

SERIAL NO: 09/731,789

FILED: DECEMBER 8, 2000

FOR: DIAMOND SEMICONDUCTOR AND DIAMOND
SEMICONDUCTOR LIGHT-EMITTING DEVICE ...

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: GROUP ART UNIT: 2814

:

: EXAMINER: DOAN, THERESA

9/A
S. M. M. M.
5-9-03

RECEIVED
MAY - 7 2003
TECHNOLOGY CENTER 2800

AMENDMENT UNDER 37 C.F.R. § 1.111

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Official Action dated November 4, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend the claims to read as shown in the clean form below:¹

1. (Amended) A diamond semiconductor having an exciton light-emission intensity characteristic that varies nonlinearly, said diamond semiconductor being fabricated using a raw gas including a methane gas and a hydrogen gas in a microwave plasma chemical vapor deposition method, in which the methane gas has a concentration of not more than 2.0%.

7. (Amended) A diamond semiconductor light-emitting device comprising:

¹The changes being made to the claims are shown using underlining and bracketing in the marked-up copy attached herewith.

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